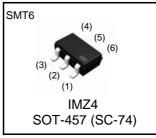
Tr1
32V
500mA
Tr2
-32V
-500mA

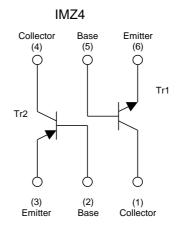
●Outline



Features

- 1) Both a 2SA1036K chip and 2SC2411K chip in a SMT6 package.
- 2) Mounting possible with SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.
- 5) Lead Free/RoHS Compliant.

Inner circuit



Application

Driver circuit

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
IMZ4	SMT6	2928	T108	180	8	3,000	Z4

•Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Val	Unit		
Faranieter	Symbol	Tr1	Tr2	Onit	
Collector-base voltage	V _{CBO}	40	-40	V	
Collector-emitter voltage	V _{CEO}	32	-32	V	
Emitter-base voltage	V _{EBO}	5	-5	V	
Collector current	I _C	500	-500	mA	
	I _{CP} ^{*1}	1	-1	А	
Collector Power dissipation	P _D ^{*2}	300 (Total) ^{*3}		mW	
Junction temperature	Tj	150		°C	
Range of storage temperature	T _{stg}	-55 to +150		°C	

•Electrical characteristics (Ta = 25°C)

<tr1></tr1>						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV_{CBO}	I _C = 100μA	40	-	-	V
Collector-emitter breakdown voltage	BV_{CEO}	I _C = 1mA	32	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = 100μA	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 20V	-	-	1.0	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 4V$	-	-	1.0	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C / I _B = 500mA / 50mA	-	-	0.6	V
DC current gain	h _{FE}	V_{CE} = 3V, I _C = 100mA	180	-	390	-
Transition frequency	f _T	$V_{CE} = 5V, I_E = -20mA,$ f = 100MHz	-	250	-	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0A,$ f = 1MHz	-	6.5	-	pF
<tr2></tr2>						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C = -100 \mu A$	-40	-	-	V
Collector-emitter breakdown voltage	BV_{CEO}	I_{C} = -1mA	-40	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	$I_C = -100 \mu A$	-5	-	-	V
Collector cut-off current	I _{CBO}	$V_{CB} = 20V$	-	-	-1.0	μA
						•
Emitter cut-off current	I _{EBO}	$V_{EB} = 4V$	-	-	-1.0	μA
Emitter cut-off current Collector-emitter saturation voltage		V _{EB} = 4V I _C / I _B = 500mA / 50mA	-	-	-1.0 -0.6	
	I _{EBO}					μA
Collector-emitter saturation voltage	I _{EBO} V _{CE(sat)}	I _C / I _B = 500mA / 50mA	-	-	-0.6	μA V

*1 P_W =10ms. Single Pulse.

*2 Each terminal mounted on a reference footprint

*3 200mW per element must not be exceeded.

●Electrical characteristic curves(Ta = 25°C)

<Tr1>

Fig.1 Ground Emitter Propagation Characteristics

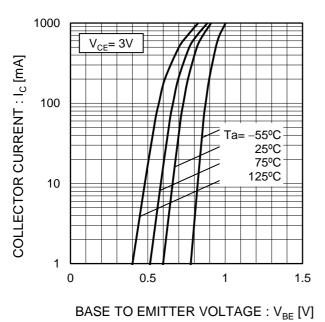


Fig.3 DC Current Gain vs. Collector Current (I)

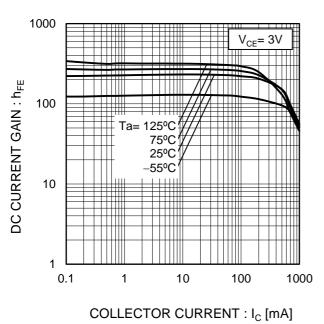


Fig.2 Typical Output Characteristics

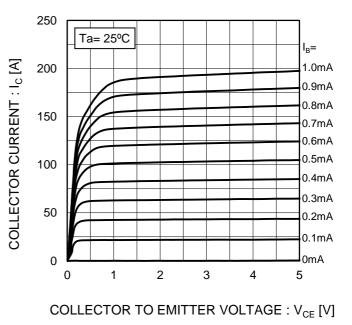
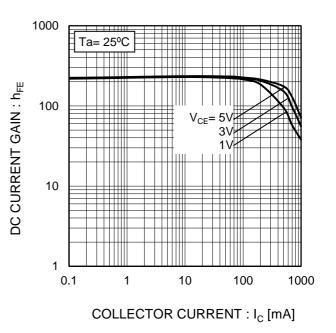
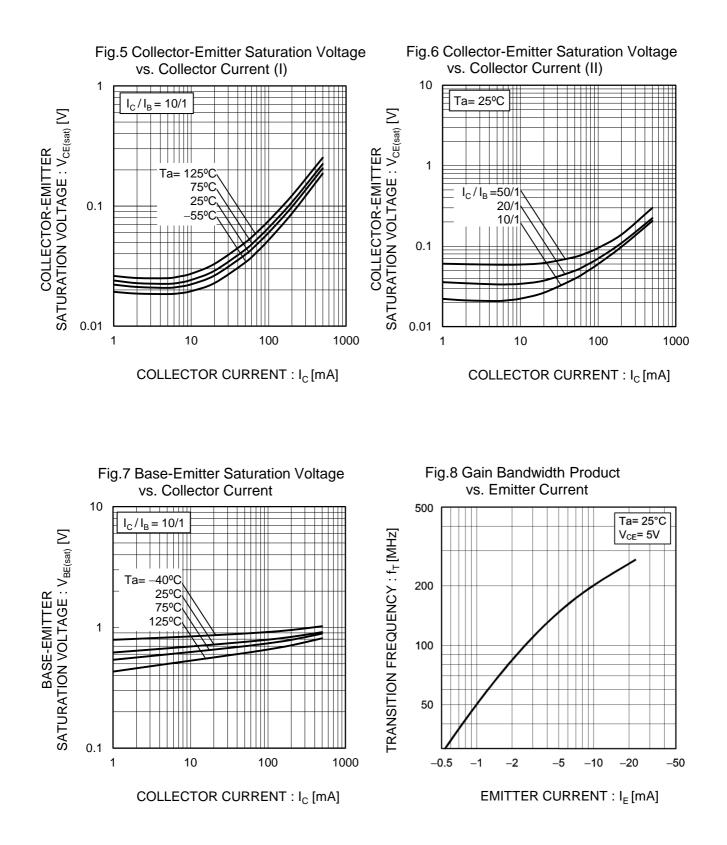
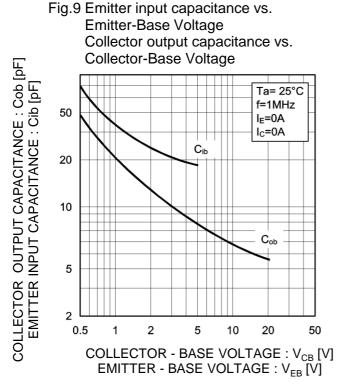


Fig.4 DC Current Gain vs. Collector Current (II)

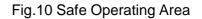


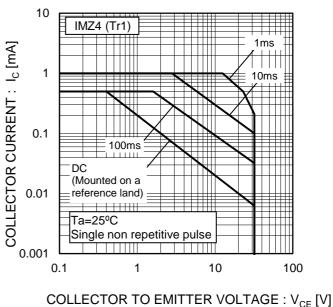






•Electrical characteristic curves(Ta = 25°C)



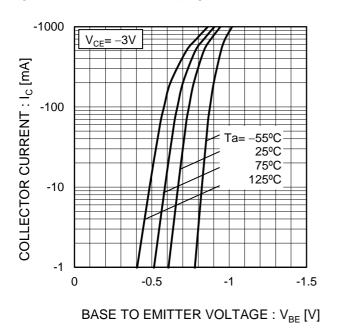


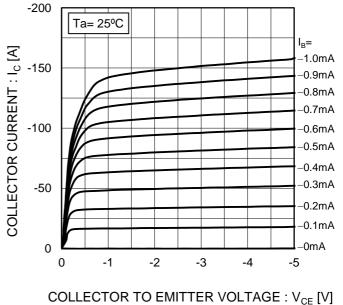
<Tr2>

IMZ4

Fig.11 Ground Emitter Propagation Characteristics

Fig.12 Typical Output Characteristics





•Electrical characteristic curves(Ta = 25°C)

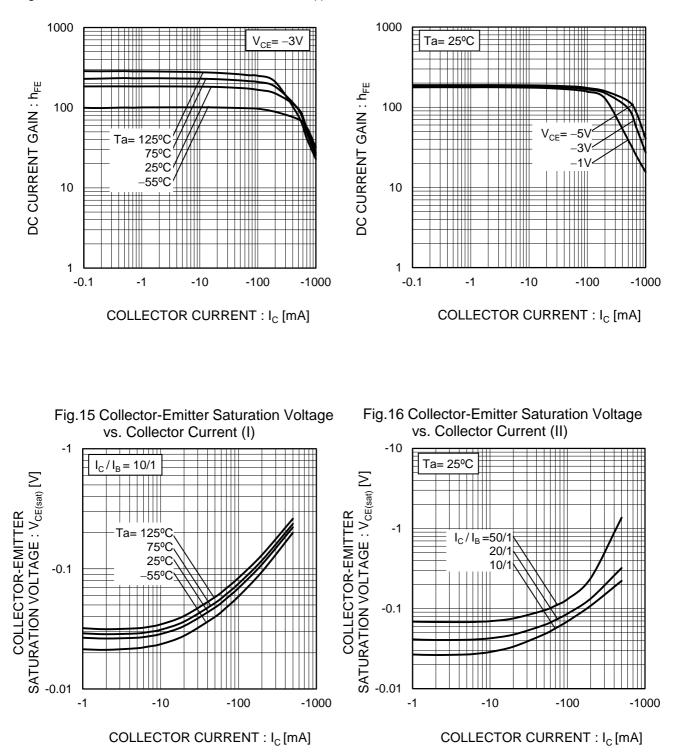
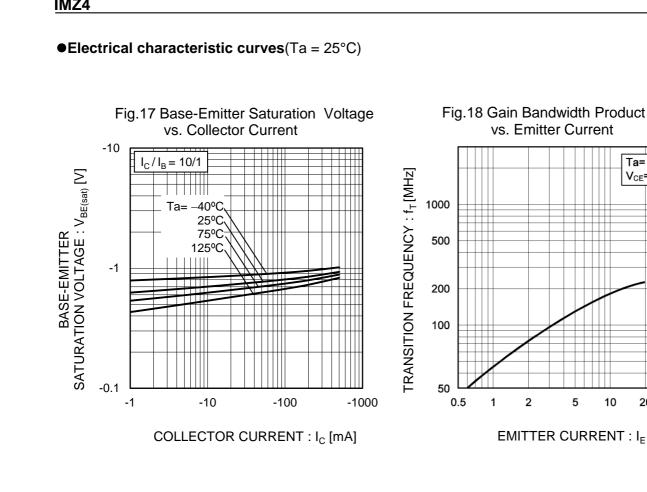


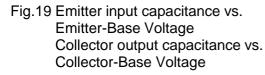
Fig.13 DC Current Gain vs. Collector Current (I)

Fig.14 DC Current Gain vs. Collector Current (II)

Ta= 25°C

 $V_{CE} = -5V$





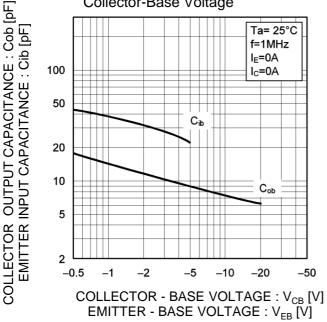


Fig.20 Safe Operating Area

2

5

EMITTER CURRENT : IE [mA]

10

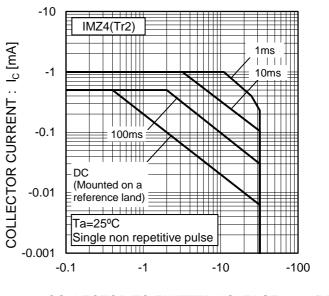
20

50

0.5

1

vs. Emitter Current

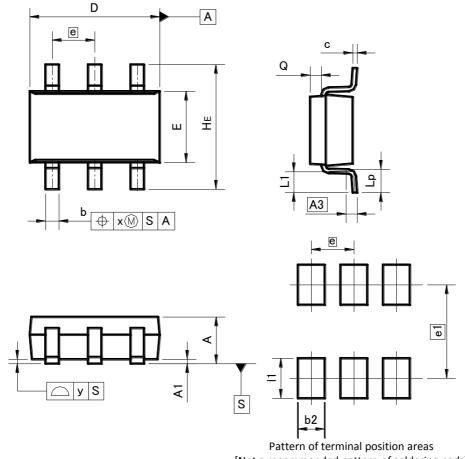


COLLECTOR TO EMITTER VOLTAGE : V_{CE} [V]

IMZ4

•Dimensions (Unit : mm)

SMT6



[Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.:	0.25 0.010		10
b	0.25	0.40	0.010	0.016
с	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
ш	1.50	1.80	0.059	0.071
e	0.95		0.0	37
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х	_	0.20	-	0.008
У	_	0.10	_	0.004

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b2		0.60	-	0.024	
e1	2.10		0.0	83	
1	_	0.90	_	0.035	

Dimension in mm / inches

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